Silicon PNP Power Transistors 2SB1033

DESCRIPTION

- With TO-220 package
- Complement to type 2SD1437

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

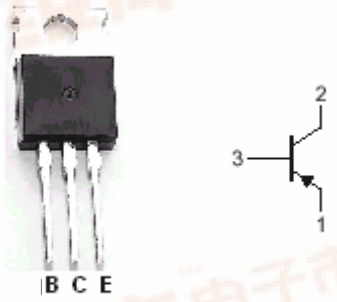

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-3	A
P_T	Total power dissipation	T_C=25℃	40	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Base-emitter breakdown voltage	I_C=-25mA ,I_B=0	-60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA ,I_E=0	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA ,I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2A; I_B=-0.2A			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-2A; I_B=-0.2A			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-60V; I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-10	μA
h_{FE}	DC current gain	I_C=-0.5A ; V_{CE}=-5V	60		320	
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-5V		12		MHz
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=-10V ;f=1MHz		100		pF

◆ **h_{FE} Classifications**

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

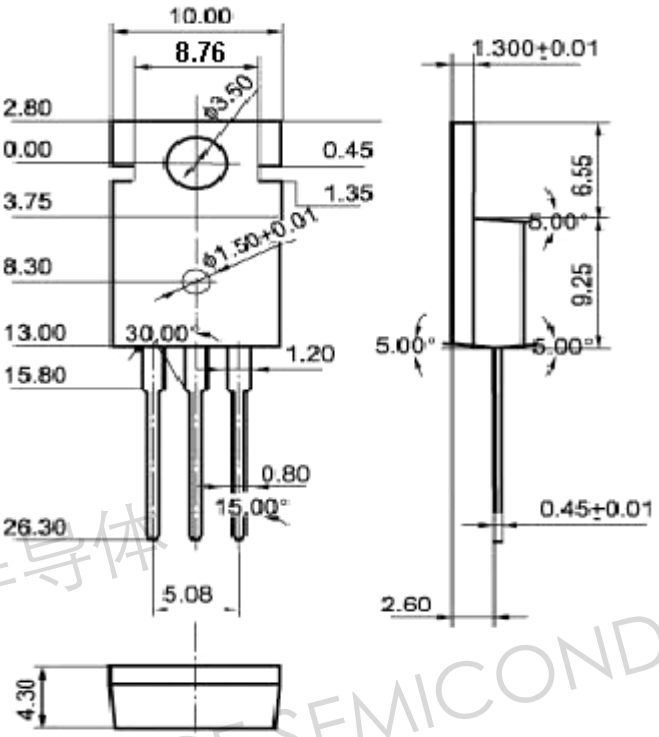

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)